

Phase transitions in a spinless, extended Falicov-Kimball model on the triangular lattice

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A numerical diagonalization technique with canonical Monte-Carlo algorithm is used to study the phase transitions from low temperature (ordered) phase to high temperature (disordered) phase of spinless Falicov-Kimball model on a triangular lattice with correlated hopping (t'). It is observed that the low temperature phases (i.e. regular, bounded, striped and segregated) persist up to a finite critical temperature (T_c). In addition, we observe that the critical temperature decreases with increasing the correlated hopping in regular, striped and bounded phases whereas it increases in the segregated phase. Single and multi peak patterns seen in the temperature dependence of specific heat (C_v) and charge susceptibility (χ) for different values of parameters like on-site Coulomb correlation strength (U), correlated hopping (t') and filling of localized electrons (n_f) are also discussed.

PACS numbers:

I. INTRODUCTION

The study of correlated systems like transition-metal dichalcogenides¹⁻³, cobaltates⁴, GdI_2 ^{5,6} and its doped variant GdI_2H_x ⁷ have attracted considerable attention recently as they exhibit a number of remarkable cooperative phenomena, like valence and metal insulator transition, charge and magnetic order, excitonic instability¹ and possible non-Fermi liquid states^{6,8}. It has been suggested recently that these correlated systems may very well be described by an effective Falicov-Kimball model (FKM) on a triangular lattice⁶. These systems are geometrically frustrated. The frustration gives rise to a large degeneracy at low temperatures and competing ground states close by in energy. A consequence of this is a fairly complex ground state magnetic phase diagram⁷ and the presence of soft local modes strongly coupled to the conduction electrons⁶.

The usual FKM⁹ was proposed to study the semiconductor-metal transition in SmB_6 and other correlated electron systems. The FKM considers only the kinetic energy of the itinerant electrons and the local Coulomb interaction between the itinerant and localized electrons. The effective interactions in the FKM are mediated by the itinerant electrons^{10,11}. Therefore, the FK model can be used to model crystallization in the solids¹¹. This model has been applied to different types of lattices (bipartite/non-bipartite) and in different dimensions. More results are available for the FKM on bipartite lattices¹²⁻¹⁷ than on non-bipartite lattices.

Recently several new ground states were observed for an extended FKM on a triangular lattice where the effect of correlated hopping t' , was taken into account¹⁸. As we know FKM is applicable to the systems where both itinerant as well as localized electrons are present. In the following, we will denote itinerant electrons as d -electrons and localized electrons as f -electrons. The correlated hopping term is influenced by the number of localized electrons present on the neighboring sites as explained below. For example, in some rare earth compounds (es-

pecially the mixed-valence compounds), the rare earth ions with two different ionic configurations f^n and f^{n-1} have different ionic radii. The ions with f^{n-1} configuration have less screening of nuclear charge as compared to the ions with f^n configuration. The d -orbitals in ions having f^{n-1} configuration feel more attraction due to the nucleus and hence get contracted. This leads to increased localization of those orbitals. Hence the d -orbital overlap between nearest neighbors depends on local f -electron occupation of neighboring ions, resulting in a correlated hopping of d -electrons. Such a correlated hopping term also appears in the first principles calculation¹⁹ of the tight binding Hamiltonian and is usually neglected in Hubbard type models for being smaller compared to the on-site term. Its significance in superconductivity has been emphasized already^{20,21} and in the context of FKM, it has been considered by several authors²²⁻²⁴ using various approximations.

We, therefore, extend the model to include a correlated hopping term in the Hamiltonian for the itinerant electrons.

$$H = - \sum_{\langle ij \rangle} (t_{ij} + \mu \delta_{ij}) d_i^\dagger d_j + E_f \sum_i f_i^\dagger f_i + U \sum_i f_i^\dagger f_i d_i^\dagger d_i + \sum_{\langle ij \rangle} t'_{ij} (f_i^\dagger f_i + f_j^\dagger f_j) d_i^\dagger d_j. \quad (1)$$

here $d_i^\dagger, d_i$ ($f_i^\dagger, f_i$) are, respectively, the creation and annihilation operators for d -electrons (f -electrons) at the site i and μ is the chemical potential. The first term in Eq.(1) is a measure of kinetic energy of d -electrons on a triangular lattice. The $t_{ij} = t$, if i and j are nearest neighboring sites and $t_{ij} = 0$, otherwise. The second term represents the dispersionless energy level E_f of f -electrons while the third term is the on-site Coulomb repulsion between d - and f -electrons. The last term (i.e. the correlated hopping term) is an extension of the usual FKM as discussed above.

A comprehensive study of the ground state phase diagram of spinless Falicov-Kimball model on a triangular

lattice with correlated hopping at different commensurate fillings of localized electrons in $(n_f - t')$ plane is reported elsewhere¹⁸. With correlated hopping ($t' \in [-1, 1]$) two different phases are observed at $\frac{1}{4}$ -filling of localized electrons namely (i) regular and (ii) segregated phases for $U = 1, 3$ and 5 . At $\frac{1}{2}$ -filling of localized electrons (i) bounded (ii) axial striped and (iii) segregated phases for $U = 1$ and (i) striped and (ii) segregated phases for $U = 5$ are reported. Some of these charge ordered phases are also observed experimentally in the above mentioned systems. Now, question arises, what is the temperature stability of these phases and which type of the phase transition occurs from the low temperature ordered phase to the high temperature disordered phase. In this work, therefore, we study the half filled FKM in its spinless version for different range of interactions with correlated hopping t' , on a triangular lattice numerically and observe the stability of these phases and type of the phase transition at finite temperature.

II. METHODOLOGY

In the extended Falicov-Kimball Hamiltonian (1), hybridization between d - and f -electrons is absent. Therefore, the local f -electron occupation number $\hat{n}_{f,i} = f_i^\dagger f_i$ commutes with H . The $\omega_i = f_i^\dagger f_i$ is a good quantum number taking values either 1 or 0 according to the site i is occupied or unoccupied by f -electron. The gauge symmetry also implies²⁵ that interband excitonic averages of the type $\langle d_i^\dagger f_j \rangle$ are identically zero at any finite temperature (implying an absence of homogeneous mixed valence) and the f -electron level remains dispersionless ($\langle f_i^\dagger f_j \rangle = 0$, for $i \neq j$). Following the local conservation of f -electron number the Hamiltonian may be written as,

$$H = \sum_{\langle ij \rangle} h_{ij}(\omega) d_i^\dagger d_j + E_f \sum_i \omega_i \quad (2)$$

where $h_{ij}(\omega) = [-t_{ij} + t'_{ij}(\omega_i + \omega_j)] + (U\omega_i - \mu)\delta_{ij}$.

We work at half-filling, i.e., $N_f + N_d = N$, where N_f, N_d are the total number of f - and d -electrons and $N = L^2$ ($L = 12$) is the number of sites. For a lattice of N sites, the Hamiltonian H is now an $N \times N$ matrix for a fixed configuration ω . We set the value of $t_{ij}=1$ for nearest neighboring sites i and j and zero, otherwise. We choose a particular value of N_f ($0 \leq N_f \leq N$), and a configuration $\omega = \{\omega_1, \omega_2, \dots, \omega_N\}$ for N_f . Choosing values for t' and U , the eigenvalues λ_i of $H(\omega)$, are calculated by numerical diagonalization with the periodic boundary conditions (PBC). Average value of the physical quantities is calculated by Monte Carlo sampling method. The details of the method is reported elsewhere^{18,26-28}.

The partition function is written as

$$Z = \prod_i \left(\sum_{\omega_i=0,1} \text{Tr} e^{-\beta H(\{\omega_i\})} \right) \quad (3)$$

where the trace is taken over the d -electrons, and $\beta = \frac{1}{kT}$. The trace is calculated from the eigenvalues λ_i ($i = 1 \dots N$) of the matrix h (first term in H (Eq.(2)). The partition function can, therefore, be recast in the form

$$Z = \prod_i \left(\sum_{\omega_i=0,1} e^{-\beta E_f \omega_i} \right) \prod_j^N (1 + e^{-\beta [\lambda_j(\omega) - \mu]}) \quad (4)$$

The corresponding total internal energy is

$$E(\omega) = \sum_i \frac{\lambda_i(\omega)}{[e^{(\lambda_i(\omega) - \mu)/kT} + 1]} + N_f E_f \quad (5)$$

The thermodynamic quantities are calculated by the averages with the statistical weights,

$$A(\omega) = \frac{1}{Z} e^{-\beta E(\omega)}, \quad (6)$$

of localized f -electron configurations ω , respectively.

In the simulations, one starts with random configuration (of f -electrons) at high temperature and then the temperature is ramped down slowly until a stable ground state is obtained at very low temperature. Then this ground state configuration is chosen as the initial configuration for a particular finite temperature. For a fixed finite temperature a large number of Monte Carlo steps are carried out to make the system reach the equilibrium. We have observed that around 1000 Monte Carlo steps are sufficient for this. Then the ensemble average of the thermodynamic quantity of interest is calculated on next (~ 4000) Monte Carlo steps. Now an important question arises whether the system has reached equilibrium or not. To ensure this we rerun the simulation starting from two different initial configurations; firstly from a fully ordered configuration of f -electrons and secondly from random configuration of f -electrons. After a certain number of Monte Carlo steps (around 1000 steps) the internal energies for both the cases approach same value. This implies that the system has reached equilibrium. A similar approach was earlier employed in the study of phase transitions in FKM on a square lattice^{17,29}.

In order to determine the type of phase transition, we have calculated temperature dependence of the charge susceptibility χ and the specific heat C_v . The χ and C_v are calculated by the fluctuation-dissipation theorem (FDT). The χ is related through the FDT to the first order variance of the density-density correlation function¹⁷, given as,

$$\chi = \frac{1}{kT} (\langle g_{n=1}^2 \rangle - \langle g_{n=1} \rangle^2), \quad (7)$$

where $\langle \dots \rangle$ represent average over different configurations. The g_n is the density-density correlation function defined as,

$$g_n = \frac{1}{N} \sum_i \sum_{\tau_1, \tau_2 = \pm n} \omega(\mathbf{r}_i) \omega(\mathbf{r}_i + \tau_1 \hat{x} + \tau_2 \hat{y}), \quad (8)$$

where $\omega(\mathbf{r}_i) = \omega_i$, $\hat{a}_x$ and $\hat{a}_y$ are the unitary vectors along the x and y directions respectively (here we assumed lattice constant as unity).

The specific heat (C_v) is related through the FDT to the internal energy and defined as,

$$C_v = \frac{1}{N} \frac{1}{kT^2} (\langle E^2 \rangle - \langle E \rangle^2) \quad (9)$$

The specific heat and charge susceptibility are calculated by different approaches. The specific heat is calculated from eigenvalues of the d -electron Hamiltonian. The d -electron spectrum changes with temperature. Correspondingly total internal energy of d -electrons changes with temperature. This change in total internal energy of the system with temperature is nothing but temperature dependence of the specific heat. It has been seen that in a particular temperature range a few eigenvalues in the lower part of d -band increase with increase in temperature (while other eigenvalues are remaining unaffected). This manifest in the increase of d -electron specific heat around that temperature. The charge susceptibility is calculated from density-density correlation function (g_n). The g_n depends on f -electron configuration only.

In addition, we have calculated the thermal average (or the ensemble average) of the f -electron occupation ($\omega_i(T)$) on each site ($i = 1$ to N) and probability energy distribution at a temperature T ($P(E, T)$ or simply $P(E)$). The $\omega_i(T)$ on each site (i) is given as,

$$\omega_i(T) = \langle \omega_i \rangle = \frac{\sum_j \omega_i e^{-\beta E(\{\omega_j\})}}{\sum_j e^{-\beta E(\{\omega_j\})}}, \quad (10)$$

where, summation is taken over the different Monte Carlo simulation steps at a finite temperature. We have chosen a random configuration of f -electrons initially. At $T = 0$ an ordered ground state configuration of f -electrons is obtained. At a finite temperature T , this ordered configuration is chosen as initial configuration. The ensemble average of the f -electron occupation, $\omega_i(T)$, is calculated for ~ 4000 Monte Carlo steps, after the system reached equilibrium.

$P(E)$ is defined as the probability of energy E occurring at temperature T in the Monte-Carlo simulation³⁰. It is equal to the thermal average of the density of states:

$$P(E, T) = \frac{n(E) e^{-E/kT}}{\sum_{E'} n(E') e^{-E'/kT}}, \quad (11)$$

where $n(E)$ is the density of states for energy E (the number of configurations with energy E) and T is the temperature of the simulation.

III. RESULTS AND DISCUSSION

At finite temperature, only few exact calculation results are available on the bipartite (square) lattice without¹⁷ and with³¹ correlated hopping. Without correlated

hopping (usual FKM) and for half-filled case, they observed that for all finite Coulomb correlation $U > 0$ the ground state configuration is checkerboard type that persist up to a critical temperature $T_c(U)$. At T_c the system undergoes a phase transition to the homogeneous phase. The phase transition is of first order for $U \leq 1$ and of second order for $U > 1$ ^{17,31}. With correlated hopping t' and $U = 0.5$, low temperature phase is an ordered phase and mainly type of checkerboard, axial striped and segregated phase. For $U = 0.5$, and for $-1.0 \leq t' \leq 0.55$ the phase transition is of the first order and for $t' > 0.55$, phase transition is of the second order. In the regime of t' , where phase is of the checkerboard type critical temperature reduces with increasing t' and in the regime where phase is of the type of axial striped and segregated, the critical temperature enhanced with increase in the t' .

Perturbative results for large U indicate that to order $1/U$, the FKM can be mapped onto an Ising antiferromagnet (AFM) in a magnetic field, $H_{eff} = \sum_{\langle ij \rangle} \frac{t^2}{4U} s_i s_j + \frac{1}{2}(\mu + E_f) \sum_i s_i + \text{constant terms}$, where $s_i = 2\omega_i - 1$, $s_i = -1, 1$. The Ising AFM state on a triangular lattice is frustrated and leads to large degeneracies at low temperature. It turns out that this frustration is lifted³² in higher order perturbation in $1/U$. It is therefore quite intriguing that one would expect the effects of frustration to bear on the finite temperature states as on-site Coulomb correlation (U) between d - and f -electrons and the chemical potential (μ) are varied.

There is hardly any exact result for the FKM on the non-bipartite lattice at finite temperature³³. Therefore, it is quite interesting to observe the temperature induced phase transitions in the FKM on a triangular lattice. We have studied the finite temperature induced phase transitions as a function of a range of values of U and fillings (i) $n_f = N_f/N = \frac{1}{4}$ and (ii) $n_f = \frac{1}{2}$ (N_d is constrained to $N - N_f$) of f -electrons using the method outlined in the previous section. We look at the effect of correlated hopping of d -electrons on phase transitions for several values of $t' \in [-1, 1]$ at a fixed U .

A. $n_f = \frac{1}{4}$ case:

In Fig.1(a) we present the variation of specific heat (C_v) and charge susceptibility (χ) with temperature for $t' = -1.0$ and $U = 1$. We observe two peak structure in C_v and χ , one at lower and other at higher temperature. Average f -electron occupation on each site ($\omega_i(T)$) given by Eq.10 at $t' = -1.0$ and $U = 1$ for different temperatures is shown in Figs.1 (b), (c) (d) and (e). The ground state configuration of f -electron is regular. This behavior of the f -electron configuration persists upto a finite temperature ~ 0.7 . Above this temperature the f -electron occupation starts to smear out. At the temperature, known as critical temperature $T_c(\sim 1.2)$, there is a second peak in C_v and χ , which really corresponds to the phase transition from regular phase to the homogeneous phase of f -electron occupation.

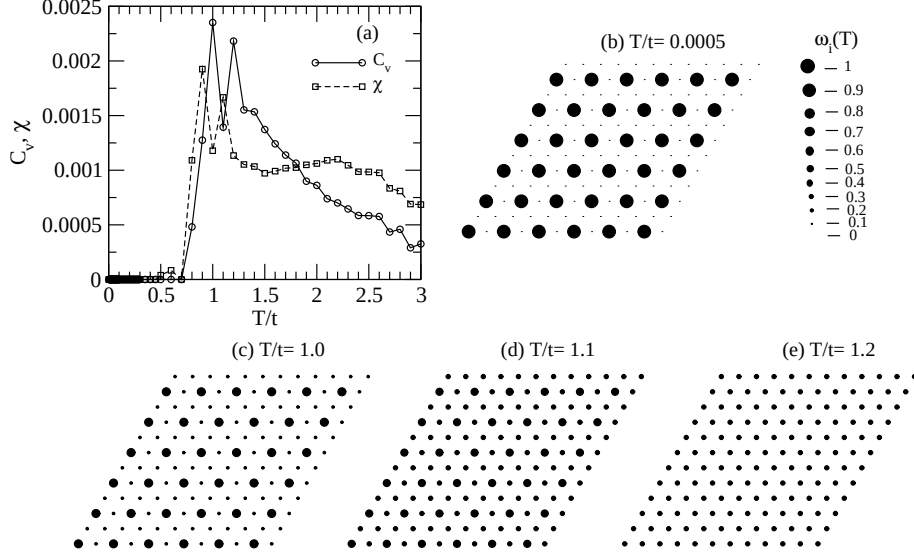


FIG. 1: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=-1.0$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

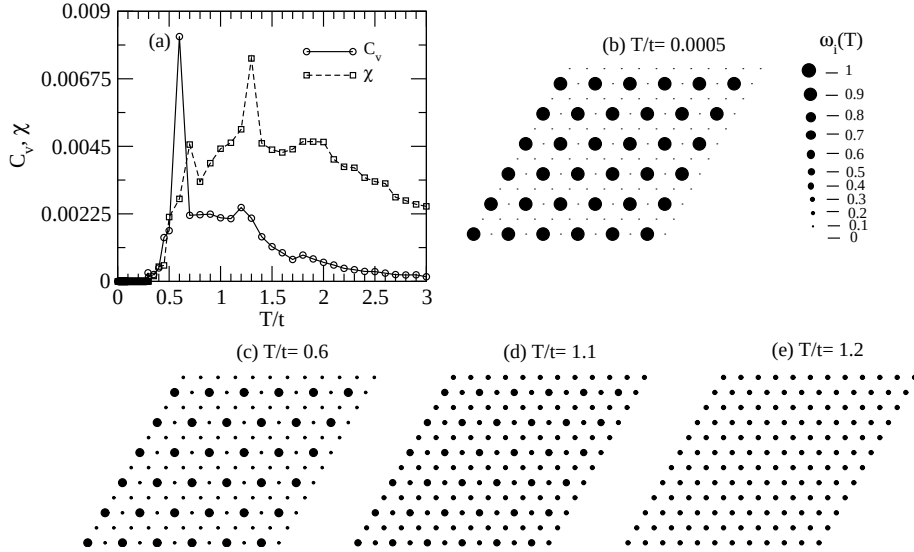


FIG. 2: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=-0.5$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

In Fig.2 we have shown the above mentioned quantities for correlated hopping $t'=-0.5$ and $U = 1$. The ground state configuration is again regular. Two peak structure is observed in C_v and χ . We observe that the critical temperature T_c , decreases with increasing t' . Behavior of both quantities C_v and χ suggest the second order phase transition (from low temperature ordered phase to high temperature homogeneous phase).

In Fig.3 we have shown the C_v , χ and $\omega_i(T)$ at different temperatures for the $t'=0$ (usual FKM⁹) and $U=1$. The probability energy distribution $P(E)$ is given in Fig.4 at

two different temperatures one at the critical and other below the critical temperature. We observe a sharp peak at $T_c \sim 0.6$ in C_v and χ which is directly related to the first order transition of the regular phase to the homogeneous phase. These features are clearly visible in the variation of $\omega_i(T)$ at different temperatures. We observe two peak structure in the $P(E)$ at critical temperature T_c . If we decrease or increase the value of temperature two peak structure disappears and a single peak structure is observed in $P(E)$. These features are in accordance with the theory of Challa, Landau and Binder³⁴, indicating

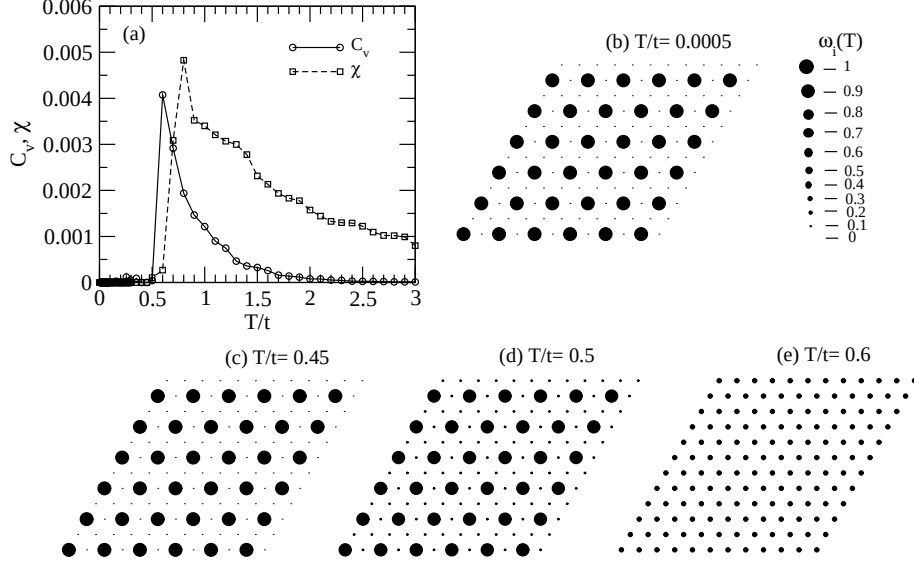


FIG. 3: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=0$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

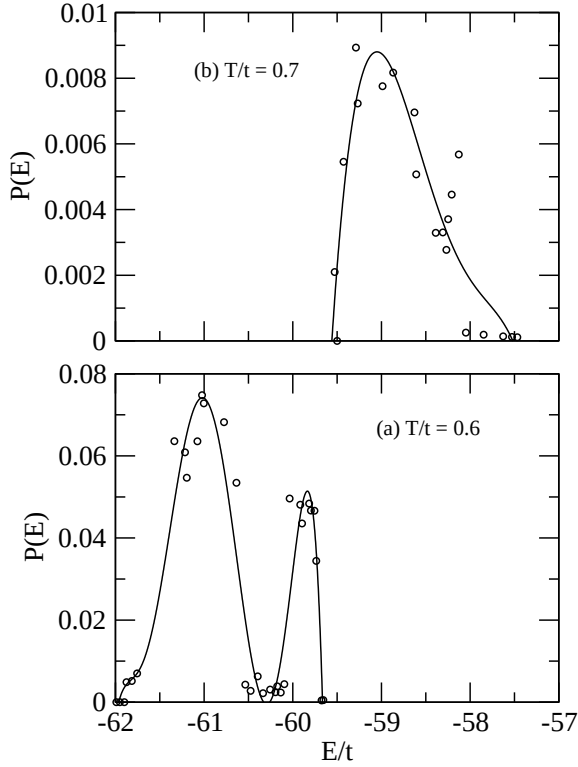


FIG. 4: Variation of probability energy distribution $P(E)$ for different temperatures ((a) to (b)) at $U=1$, $t'=0$ and $n_f = \frac{1}{4}$.

χ and $\omega_i(T)$ is shown in Fig.5 and Fig.6 for $t'=0.5$ and 1 respectively. Two peak structure is observed in C_v and χ . There is second order phase transition from segregated phase to homogeneous phase at T_c , which corresponds to the second peak in the C_v and χ . In this region the critical temperature T_c , where phase transition occurs, increases with increasing the correlated hopping t' .

In the usual FKM on bipartite lattice, second order phase transition occurs for $U > 1^{17,31}$. In order to clarify the nature of the phase transition in the usual FKM on non-bipartite lattice for $U > 1$, we have calculated temperature dependence of the C_v , χ and $\omega_i(T)$ at $U = 5$ and have shown in Fig.7. We observe multi-peak structure in C_v and χ . The ground state configuration, in the form of regular phase, persist upto a finite temperature. The second order phase transition from regular to homogeneous disordered phase occurs at $T_c = 2.3$, and corresponds to the last peak in the C_v and χ . The T_c here is very large in comparison to that at $U = 1$ ($T_c = 0.6$). Due to large intra-site Coulomb correlation between d - and f -electrons, large temperature is required to smear the occupation of f -electrons.

To observe the effect of t' on phase transition at $U = 5$, we have calculated C_v , χ and $\omega_i(T)$ at $t' \in [-1, 1]$ (shown in Fig.8, for $t' = -1.0$ only). We observe second order phase transition at all t' values. The phase transition occurs at a higher value of critical temperature in comparison to that at $U = 1$.

B. $n_f = \frac{1}{2}$ case:

the first order phase transition at T_c . With the increasing value of $t' \sim 0.4$, the ground state configuration is the segregated (also metallic) phase¹⁸. Variation of C_v ,

Three different ground state configurations namely bounded, axial striped and segregated phases are ob-

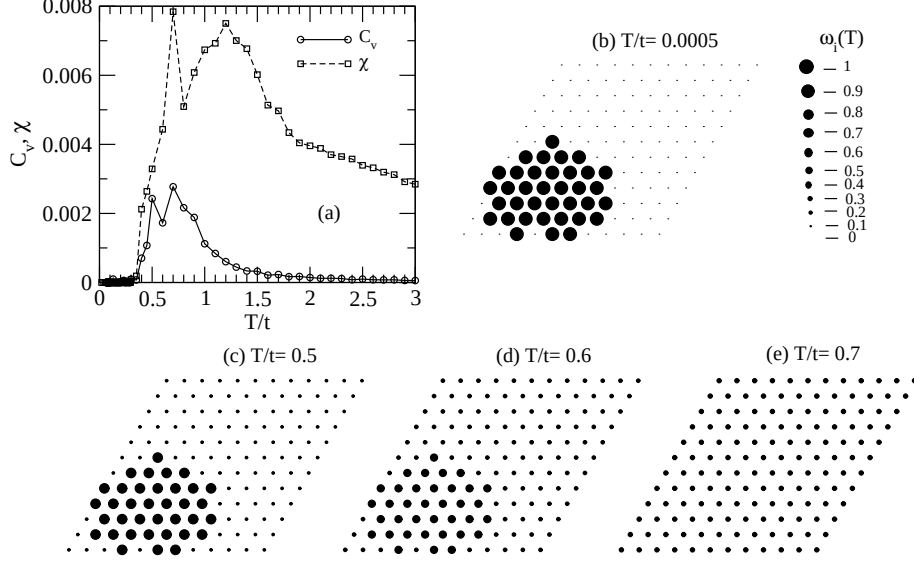


FIG. 5: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=0.5$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

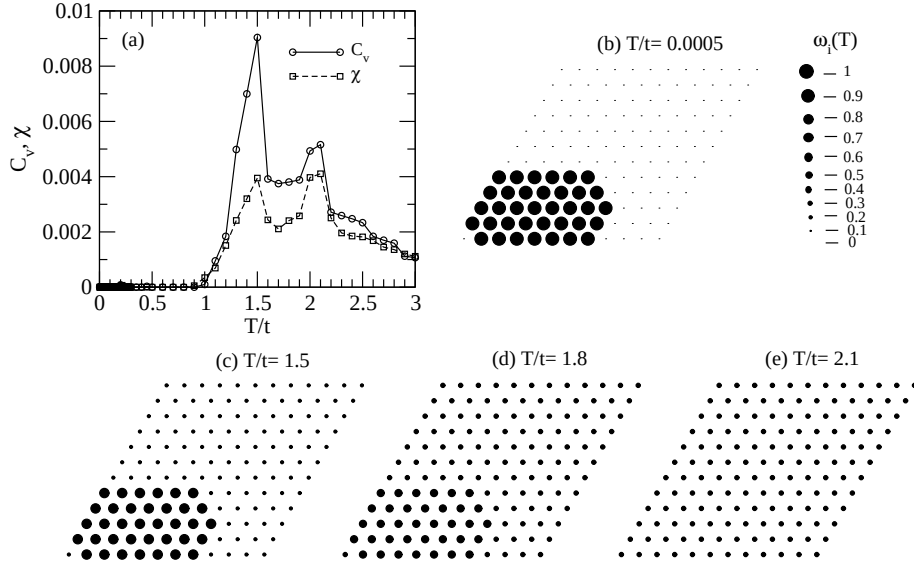


FIG. 6: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=1.0$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

served¹⁸ at $U = 1$ and $t' \in [-1, 1]$. In order to observe the stability of these phases at finite temperatures and to see the effect of filling of f -electron on T_c , we have calculated C_v , χ and $\omega_i(T)$ at $U = 1$ for $t' \in [-1, 1]$. Shown in Figs.9, 10, 11 and 12, are variation of C_v , χ and $\omega_i(T)$ for $U = 1$ and $t' = -1, 0, 0.5$ and 1 , respectively.

The ground state f -electron configuration for $t' = -1.0$ to ~ 0.4 and $U = 1$, is bounded. At finite temperature, for all negative values of t' , two peak structure is observed in C_v and χ (see Fig9(a) for $t' = -1.0$). Corresponding variation of $\omega_i(T)$ at different temperatures is shown

in Figs.9(b), (c), (d) and (e). We observe second order phase transition from low temperature bounded phase to high temperature homogeneous phase at T_c .

In usual FKM ($t' = 0$), we observe single peak structure in C_v and χ (Fig.10(a)). First order phase transition is observed at $T_c = 0.45$. Axial striped phase is observed at about $t' = 0.5$. This phase is not present at $\frac{1}{4}$ -filling. Single peak is observed in C_v and χ (Fig.11). First order phase transition from low temperature axial striped phase to finite temperature homogeneous phase is observed about $T_c = 0.275$. Phase segregation in the $(n_f - t')$

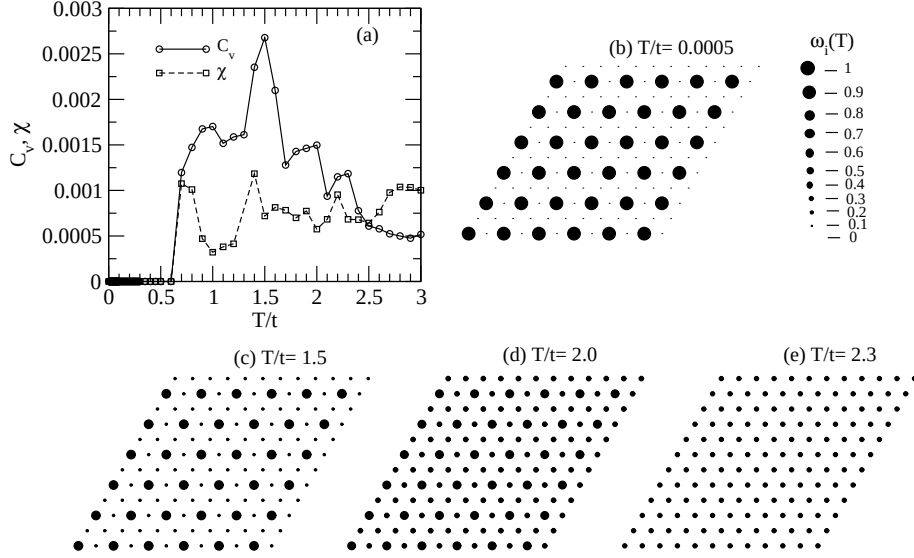


FIG. 7: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=5$, $t'=0$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

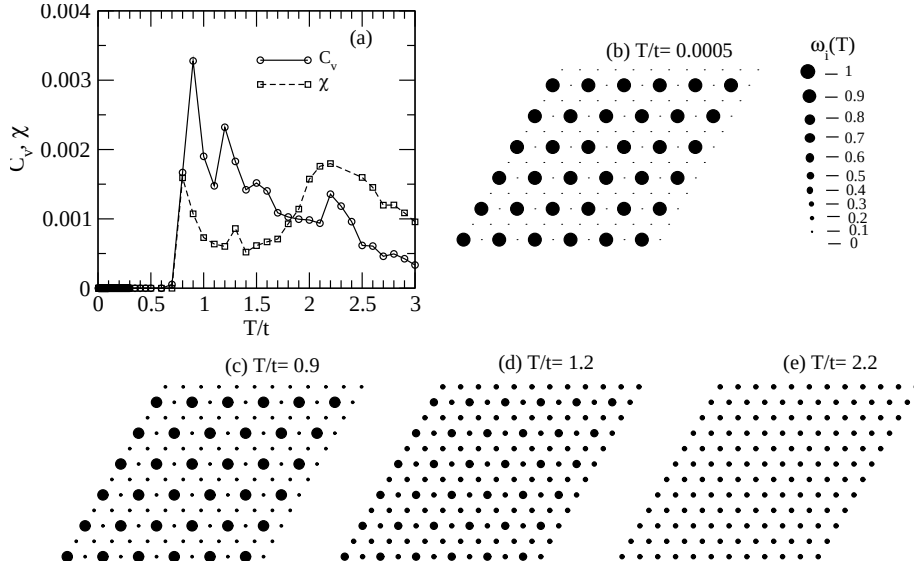


FIG. 8: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=5$, $t'=-1.0$ and $n_f = \frac{1}{4}$. Strength of the filled circles are shown in right side of upper panel.

plane is observed for $t' \geq 0.6$ ¹⁸. Variation of C_v , χ and $\omega_i(T)$ for $t'=1$ and $U = 1$ at different temperatures are shown in Fig.12. Multi-peak structure is observed in C_v and χ . Phase transition of the second order, low temperature segregated to high temperature homogeneous phase is observed at $T_c=2.3$, which corresponds to the last peak in C_v and χ . The T_c is very large in segregated phase in comparison to the other phases.

We have calculated C_v , χ and $\omega_i(T)$ for $U = 5$ and $t' \in [-1, 1]$ (not shown here). Multi-peaks are observed in C_v and χ . At all values of t' second order phase transition

from low temperature ordered phase to high temperature disordered phase about T_c (much larger than at $U = 1$), corresponding to the last peak in C_v and χ , is observed.

Shown in Fig.13 is the variation of critical temperature T_c with correlated hopping t' at $U = 1$ and $n_f = \frac{1}{4}$ and $\frac{1}{2}$. We observe, critical temperature decreases in regular, striped and bounded phases and increases in segregated phase for both fillings. The critical temperature is very large in the phase segregation in comparison to regular, bounded and striped phases.

Let us now discuss the numerical results obtained

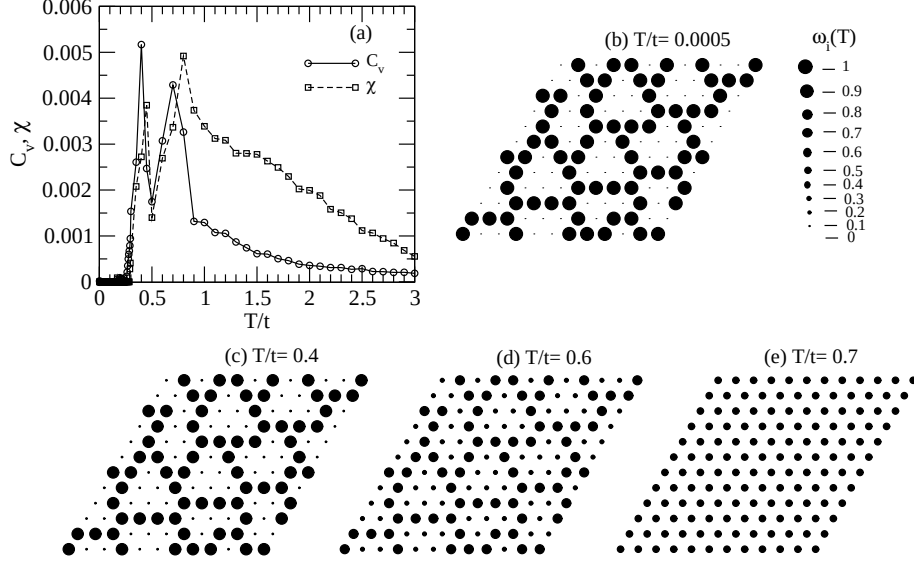


FIG. 9: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=-1.0$ and $n_f = \frac{1}{2}$. Strength of the filled circles are shown in right side of upper panel.

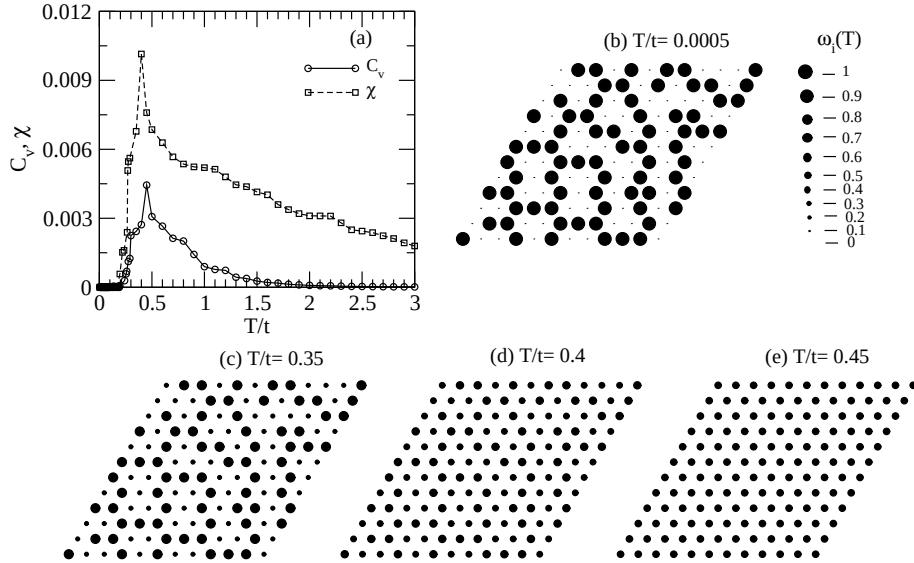


FIG. 10: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=0$ and $n_f = \frac{1}{2}$. Strength of the filled circles are shown in right side of upper panel.

above in the context of the results obtained on the bipartite lattice^{17,31} at $U = 1$, different values of t' and temperature. Important differences in numerical results of the spinless FKM on square and triangular lattices with correlated hopping are that phase transition occurs at very high temperature (around 10 times larger) in triangular lattice than in square lattice. Phase transition is of first order for negative and few positive values of t' in square lattice while in triangular lattice it is of second order for all negative values of t' . In both type of lattices, we observe that second order phase transition occurs at

large T_c than the first order phase transition. In low temperature regime, the C_v and χ decreases slowly for second order phase transition and they decrease abruptly for first order phase transition with decreasing the temperature. In triangular lattice, the critical temperature in regular, striped and bounded phases is larger for $\frac{1}{4}$ -filling in comparison to at $\frac{1}{2}$ -filling of f-electrons while nearly equal in segregated phase.

In nut shell, we have studied the phase transitions in the spinless FKM on a triangular lattice with correlated hopping t' . We have found that the ground state or-

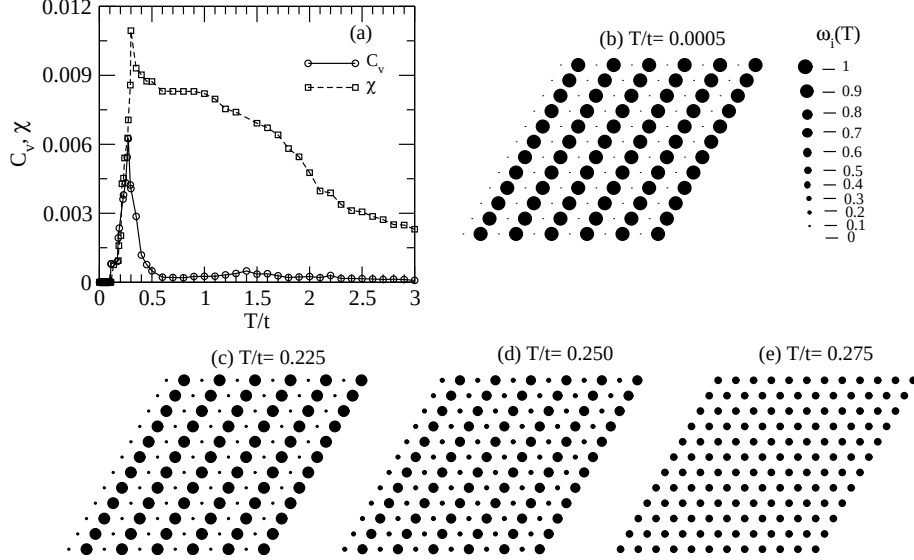


FIG. 11: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=0.5$ and $n_f = \frac{1}{2}$. Strength of the filled circles are shown in right side of upper panel.

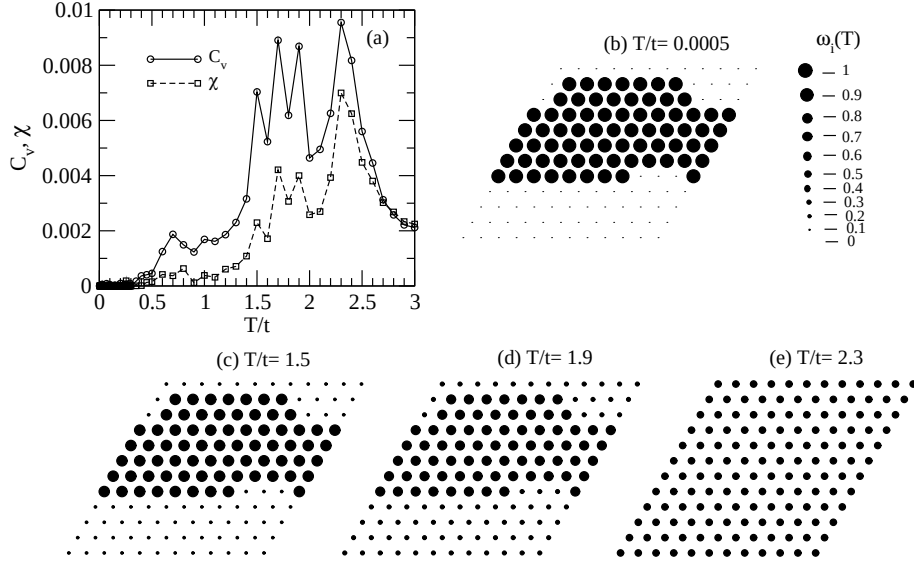


FIG. 12: The specific heat C_v and charge susceptibility χ (a) and average f-electron occupation $\omega_i(T)$ on each site ((b) to (e)) for different temperatures at $U=1$, $t'=1.0$ and $n_f = \frac{1}{2}$. Strength of the filled circles are shown in right side of upper panel.

dered configuration persist up to a finite critical temperature (T_c). Above critical temperature, homogeneous disordered phase is observed. At $U = 1$ and $\frac{1}{4}$ -filling of f -electrons, second order phase transition from regular to disordered phase is observed for negative values of t' . However, for $0 \leq t' \leq 0.4$ the same phase transition is seen to be of first order. Again a second order phase transition is observed for $t' > 0.4$ (from segregated phase to disordered). The critical temperature T_c , decreases in regular phase and increases in segregated phase with t' . At $\frac{1}{2}$ -filling of f -electrons second order phase transi-

tion is observed for negative values of t' (bounded phase to disordered). First order phase transition is observed for $0 \leq t' \leq 0.55$ (bounded and axial striped phase to disordered). Second order phase transition is observed for $t' \geq 0.6$ (segregated phase to disordered). The T_c decreases in bounded and in axial striped phase and increases in segregated phase. At half filling, segregated phase exists at higher values of t' than at one fourth filling of f -electron. Correspondingly, T_c decreases up to a higher value of t' in half filling than one fourth filling of f -electrons. The T_c , in regular and in bounded

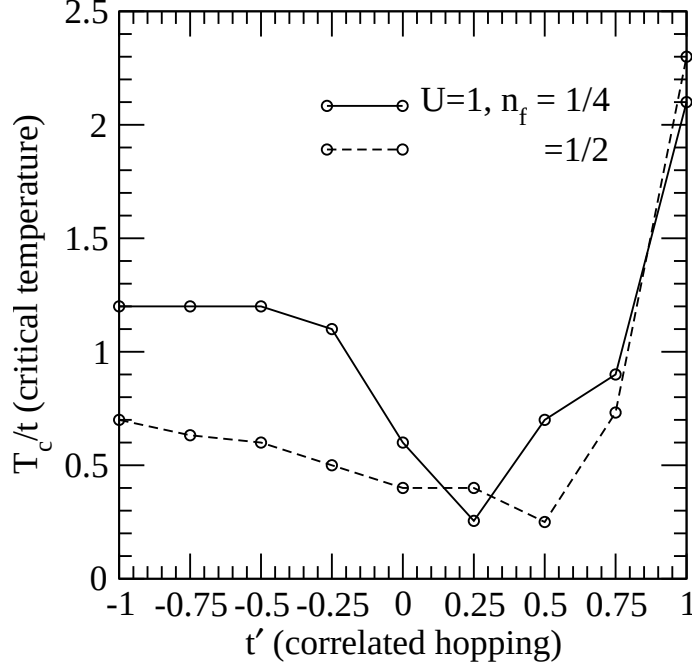


FIG. 13: Variation of critical temperature T_c with correlated hopping t' for two different fillings of f-electrons at $U=1$ and $N = 12 \times 12$.

phase is larger and similar in segregated phase for one fourth filling, in comparison to half filling of f -electrons. Second order phase transition is found for all calculated values of t' and filling of f-electrons at $U = 5$. As mentioned earlier there is rarely any numerical calculation results available for the spinless FKM on triangular systems at finite temperatures. Our results may be helpful

and motivate to experimental and theoretical study for finite temperature properties of the frustrated systems of recent interest like transition-metal dichalcogenides, cobaltates, GdI_2 , $NaTiO_2$ and $NaVO_2$ etc.

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